TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

HN1C03F

For Muting And Switching Applications

- Including two devices in SM6 (Super mini type with 6 leads)
- High emitter-base voltage: $V_{EBO} = 25V$ (min)
- High reverse hFE: reverse hFE = $150 (typ.)(V_{CE} = -2V, I_C = -4mA)$
- Low on resistance: $R_{ON} = 1\Omega$ (typ.)(IB = 5mA)

Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristic	Symbol	Rating	Unit	
Collector-base voltage	V _{CBO}	50	V	
Collector-emitter voltage	V _{CEO}	20	V	
Emitter-base voltage	V _{EBO}	25	V	
Collector current	Ι _C	300	mA	
Base current	Ι _Β	60	mA	
Collector power dissipation	P _C *	300	mW	
Junction temperature	Tj	150	°C	
Storage temperature range	T _{stg}	-55~150	°C	



* Total rating

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Electrical Characteristics (Ta = 25°C) (Q1,Q2 Common)

Characteristic Symbol		Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current		I _{CBO}	_	V _{CB} = 50V, I _E = 0	_	_	0.1	μA
Emitter cut-	off current	I _{EBO}	—	V _{EB} = 25V, I _C = 0	_	_	0.1	μA
DC current	gain	h _{FE (Note)}	—	$V_{CE} = 2V, I_C = 4mA$	200	—	1200	
Collector-emitter saturation voltage		V _{CE (sat)}	_	I _C = 30mA, I _B = 3mA	_	0.042	0.1	V
Base-emitter voltage		V _{BE}	—	$V_{CE} = 2V, I_C = 4mA$	_	0.61	_	V
Transition frequency		f _T	_	$V_{CE} = 6V, I_C = 4mA$	_	30	_	MHz
Collector output capacitance		C _{ob}	_	V _{CB} = 10V, I _E = 0, f = 1MHz	_	4.8	7	pF
Switching time	Turn-on time	_	_	$10V \xrightarrow{\text{INPUT } 4k\Omega} \xrightarrow{\text{OUTPUT}}_{C \neq} \xrightarrow{C \neq}_{T \neq} \xrightarrow{C \oplus}_{T \neq} \xrightarrow{C \neq}_{T \neq} \xrightarrow{C \to}_{T \to} $	_	160	_	
	Storage Time	_	_		_	500	_	ns
	Fall time	_	_		_	130	_	

Note: hFE Classification

A: 200~700, B: 350~1200

Marking

Equivalent Circuit (Top View)





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(Q1,Q2 Common)



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